

## TSF630M-VB Datasheet

### N-Channel 200 V (D-S) MOSFET

#### PRODUCT SUMMARY

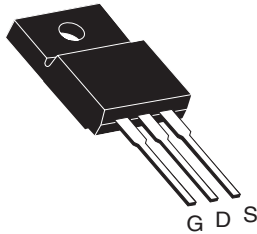
$V_{DS}$ (V)	200	
$R_{DS(on)}$ ( $\Omega$ )	$V_{GS} = 10\text{ V}$	0.265
$Q_g$ (Max.) (nC)	16	
$Q_{gs}$ (nC)	5	
$Q_{gd}$ (nC)	8	
Configuration	Single	

#### FEATURES

- Isolated Package
- High Voltage Isolation = 2.5 kV<sub>RMS</sub> ( $t = 60\text{ s}$ ;  $f = 60\text{ Hz}$ )
- Sink to Lead Creepage Distance = 4.8 mm
- 175 °C Operating Temperature
- Dynamic dV/dt Rating
- Low Thermal Resistance
- Lead (Pb)-free Available



TO-220 FULLPAK



N-Channel MOSFET

#### ABSOLUTE MAXIMUM RATINGS $T_C = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted

PARAMETER			SYMBOL	LIMIT	UNIT
Drain-Source Voltage			V <sub>DS</sub>	200	V
Gate-Source Voltage			V <sub>GS</sub>	± 20	
Continuous Drain Current	V <sub>GS</sub> at 10 V	T <sub>C</sub> = 25 °C	I <sub>D</sub>	10	A
		T <sub>C</sub> = 100 °C		6.5	
Pulsed Drain Current <sup>a</sup>			I <sub>DM</sub>	32	
Linear Derating Factor				0.24	W/°C
Single Pulse Avalanche Energy <sup>b</sup>			E <sub>AS</sub>	36	mJ
Repetitive Avalanche Current <sup>a</sup>			I <sub>AR</sub>	7.2	A
Repetitive Avalanche Energy <sup>a</sup>			E <sub>AR</sub>	3.7	mJ
Maximum Power Dissipation	T <sub>C</sub> = 25 °C		P <sub>D</sub>	37	W
Peak Diode Recovery dV/dt <sup>c</sup>			dV/dt	5.5	V/ns
Operating Junction and Storage Temperature Range			T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 175	°C
Soldering Recommendations (Peak Temperature)		for 10 s		300 <sup>d</sup>	
Mounting Torque	6-32 or M3 screw			10	lbf · in
				1.1	N · m

#### Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- $V_{DD} = 25\text{ V}$ , starting  $T_J = 25\text{ }^{\circ}\text{C}$ ,  $L = 1.0\text{ mH}$ ,  $R_G = 25\text{ }\Omega$ ,  $I_{AS} = 7.2\text{ A}$  (see fig. 12).
- $I_{SD} \leq 9.2\text{ A}$ ,  $dI/dt \leq 110\text{ A}/\mu\text{s}$ ,  $V_{DD} \leq V_{DS}$ ,  $T_J \leq 175\text{ }^{\circ}\text{C}$ .
- 1.6 mm from case.

**THERMAL RESISTANCE RATINGS**

PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	$R_{thJA}$	-	65	°C/W
Maximum Junction-to-Case (Drain)	$R_{thJC}$	-	4.1	

**SPECIFICATIONS**  $T_J = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}$ , $I_D = 250\text{ }\mu\text{A}$		200	-	-	V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^{\circ}\text{C}$ , $I_D = 1\text{ mA}$		-	0.13	-	V/ $^{\circ}\text{C}$
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$		2.0	-	4.0	V
Gate-Source Leakage	$I_{GSS}$	$V_{GS} = \pm 20\text{ V}$		-	-	$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 200\text{ V}$ , $V_{GS} = 0\text{ V}$		-	-	25	$\mu\text{A}$
		$V_{DS}=160\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_J = 150\text{ }^{\circ}\text{C}$		-	-	250	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 4.3\text{ A}^b$	-	0.265	-	$\Omega$
Forward Transconductance	$g_{fs}$	$V_{DS} = 50\text{ V}$ , $I_D = 4.3\text{ A}^b$		2.3	-	-	S
Dynamic							
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}$ , $V_{DS} = 25\text{ V}$ , $f = 1.0\text{ MHz}$ , see fig. 5		-	560	-	pF
Output Capacitance	$C_{oss}$			-	260	-	
Reverse Transfer Capacitance	$C_{rss}$			-	110	-	
Drain to Sink Capacitance	$C$	$f = 1.0\text{ MHz}$		-	12	-	
Total Gate Charge	$Q_g$	$V_{GS} = 10\text{ V}$	$I_D = 9.2\text{ A}$ , $V_{DS} = 80\text{ V}$ , see fig. 6 and 13 <sup>b</sup>	-	-	16	nC
Gate-Source Charge	$Q_{gs}$			-	-	4.4	
Gate-Drain Charge	$Q_{gd}$			-	-	7.7	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 100\text{ V}$ , $I_D= 9.2\text{ A}$ , $R_G = 18\text{ }\Omega$ , $R_D= 5.2\text{ }\Omega$ , see fig. 10 <sup>b</sup>		-	8.8	-	ns
Rise Time	$t_r$			-	30	-	
Turn-Off Delay Time	$t_{d(off)}$			-	19	-	
Fall Time	$t_f$			-	20	-	
Internal Drain Inductance	$L_D$	Between lead, 6 mm (0.25") from package and center of die contact 		-	4.5	-	nH
Internal Source Inductance	$L_S$			-	7.5	-	
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	$I_S$	MOSFET symbol showing the integral reverse p - n junction diode 		-	10	-	A
Pulsed Diode Forward Current <sup>a</sup>	$I_{SM}$			-	32	-	
Body Diode Voltage	$V_{SD}$	$T_J = 25\text{ }^{\circ}\text{C}$ , $I_S = 7.2\text{ A}$ , $V_{GS} = 0\text{ V}^b$		-	-	2.5	V
Body Diode Reverse Recovery Time	$t_{rr}$	$T_J = 25\text{ }^{\circ}\text{C}$ , $I_F = 9.2\text{ A}$ , $dI/dt = 100\text{ A}/\mu\text{s}^b$		-	130	260	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$			-	0.65	1.3	$\mu\text{C}$
Forward Turn-On Time	$t_{on}$	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S$ and $L_D$ )					

**Notes**

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).  
 b. Pulse width  $\leq 300\text{ }\mu\text{s}$ ; duty cycle  $\leq 2\%$ .

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted

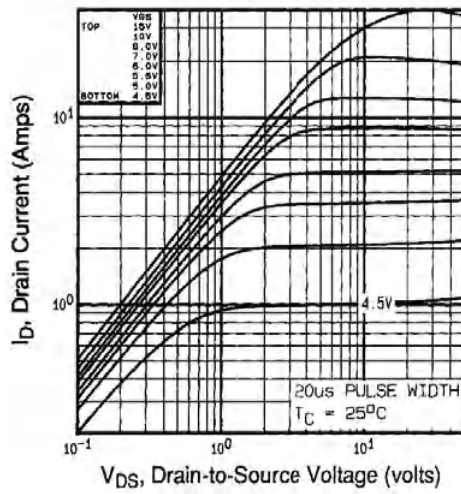


Fig. 1 - Typical Output Characteristics,  $T_C = 25\text{ }^{\circ}\text{C}$

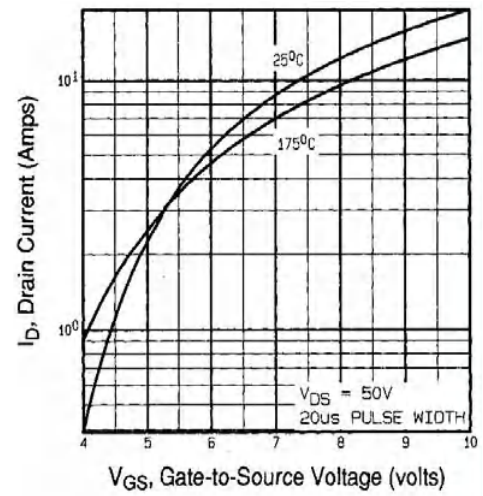


Fig. 3 - Typical Transfer Characteristics

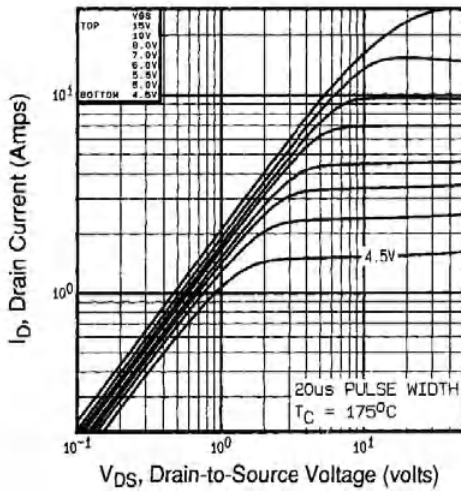


Fig. 2 - Typical Output Characteristics,  $T_C = 175\text{ }^{\circ}\text{C}$

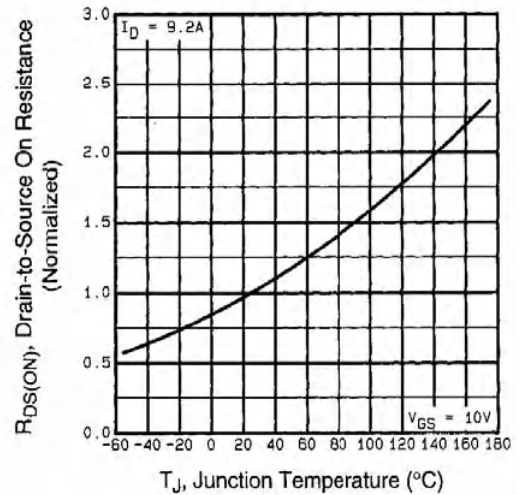


Fig. 4 - Normalized On-Resistance vs. Temperature

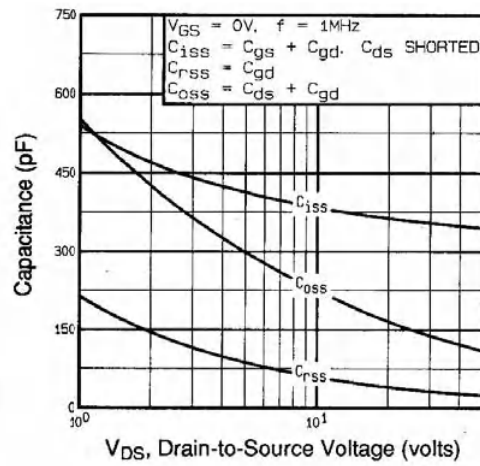


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

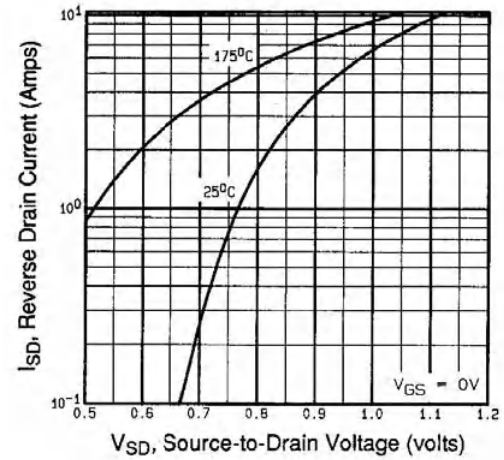


Fig. 7 - Typical Source-Drain Diode Forward Voltage

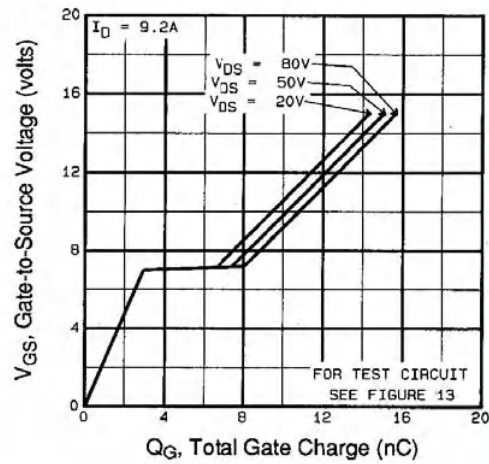


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

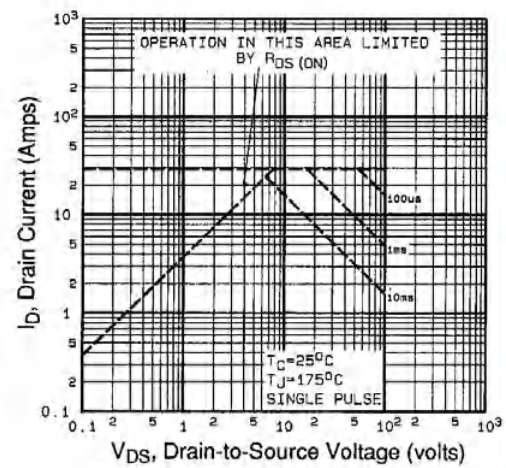


Fig. 5 - Fig. 8 - Maximum Safe Operating Area

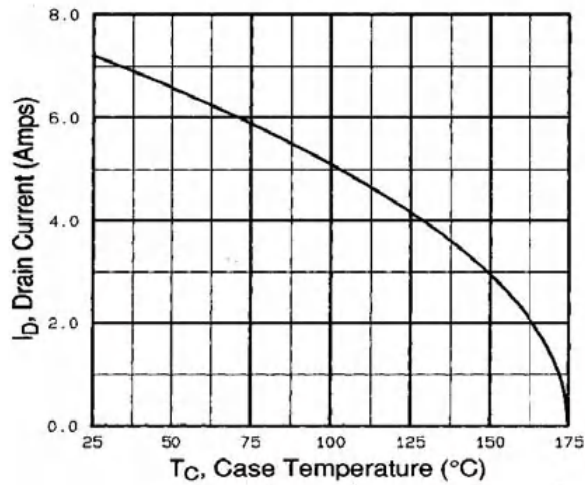


Fig. 9 - Maximum Drain Current vs. Case Temperature

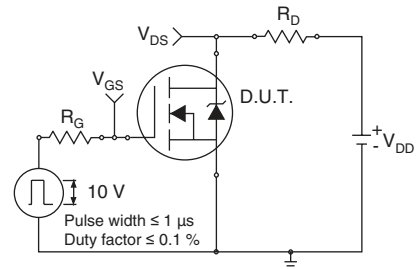


Fig. 10a - Switching Time Test Circuit

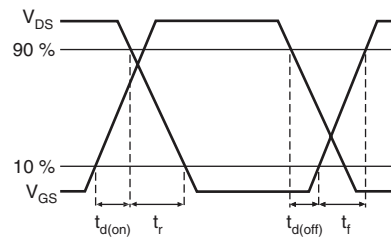


Fig. 10b - Switching Time Waveforms

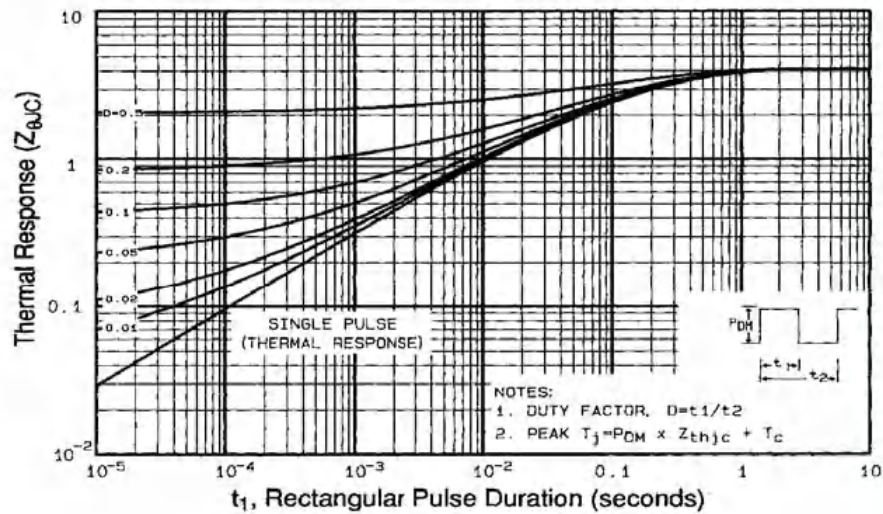


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

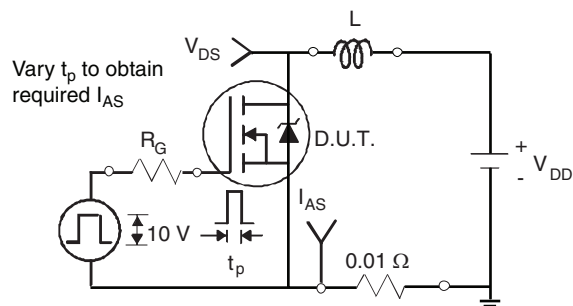


Fig. 12a - Unclamped Inductive Test Circuit

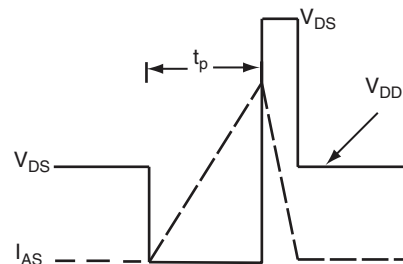


Fig. 12b - Unclamped Inductive Waveforms



Fig. 12c - Maximum Avalanche Energy vs. Drain Current

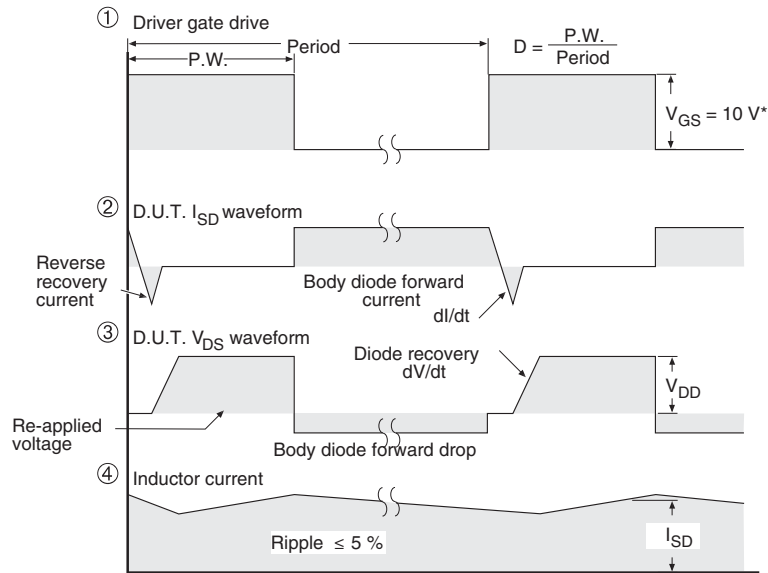
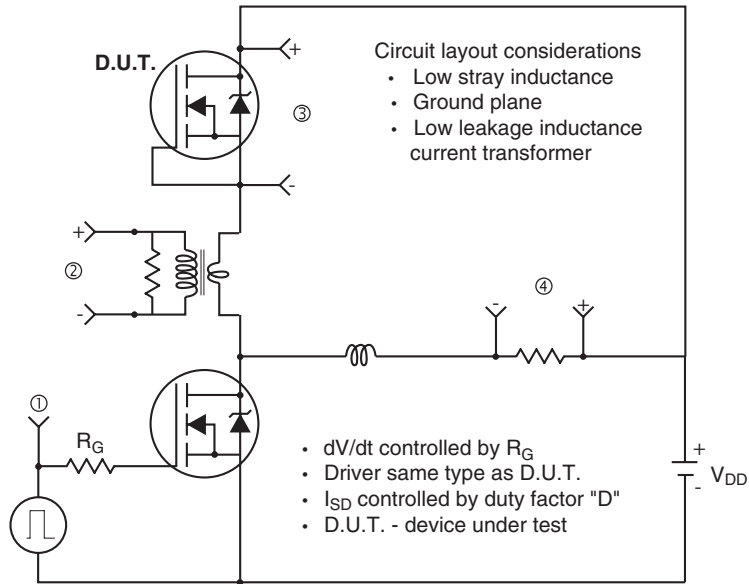


Fig. 13a - Basic Gate Charge Waveform



Fig. 13b - Gate Charge Test Circuit

### Peak Diode Recovery $dV/dt$ Test Circuit



\*  $V_{GS} = 5\text{ V}$  for logic level devices

**Fig. 14 - For N-Channel**



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